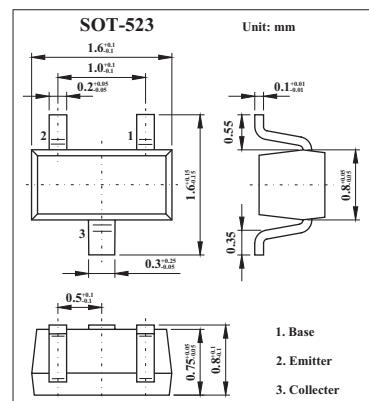


Low Frequency Transistor

2SC5585

■ Features

- Hig current.
- Low $V_{CE(sat)}$: $V_{CE(sat)} \leq 250\text{mV}$ at $I_C=200\text{mA}/I_B=10\text{mA}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	500	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = 10 \mu\text{A}$	15			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 1\text{mA}$	12			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = 10 \mu\text{A}$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=15\text{V}$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}$			100	nA
DC current gain	h_{FE}	$V_{CE}=2\text{V}, I_C=10\text{mA}$	270		680	
Collector emitter saturation voltage	$V_{CE(sat)}$	$I_C=200\text{mA}, I_B=10\text{mA}$		90	250	mV
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		7.5		pF
Transition frequency	f_T	$V_{CE}=2\text{V}, I_E=-10\text{mA}, f=100\text{MHz}$		320		MHz

■ Marking

Marking	BX
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